

In the Claims:

Claims 1-3 (cancelled)

Claim 4 (currently amended): A method for depositing micro-lenses on a semiconductive circuit comprising the steps of:

applying a first coat of micro-lens suitable material to a the surface of a the semiconductive circuit;

imparting a first lens formation pattern onto the first coat of micro-lens suitable material,
wherein the first lens formation pattern includes a boundary for each of a first plurality of micro-
lenses to be formed, and wherein the first lens formation pattern further includes a first setback
from the boundary for each of the first plurality of micro-lenses to be formed;

removing unwanted portions of the first coat of micro-lens suitable material;
forming a the first plurality of micro-lenses from the remaining first coat of microlens suitable material;

applying a second coat of micro-lens suitable material to the semiconductive circuit;
imparting a second lens formation pattern to the second coat of micro-lens suitable material, wherein the second lens formation pattern includes a boundary for each of a second
plurality of micro-lenses to be formed, and wherein the second lens formation pattern further
includes a second setback from the boundary for each of the second plurality of micro-lenses to
be formed;

removing unwanted portions of the second coat of micro-lens suitable material; and
forming a the second plurality of micro-lenses from the remaining second coat of micro-

lens suitable material.

Claim 5 (original): The method of Claim 4 wherein the first and second lens formation patterns are alternate counterparts of each other.

Claim 6 (original): The method of Claim 5 wherein the first and second lens formation patterns comprise rectangular regions in a checkerboard pattern.

Claim 7 (cancelled)

Claim 8 (original): The method of Claim 4 wherein the step of forming the first and second plurality of micro-lenses comprise the steps of:

raising the temperature of the micro-lens suitable material in order to relieve the surface tension thereof;

allowing the micro-lens suitable material to reflow in order to achieve a desired lens focal length; and

reducing the temperature of the micro-lens suitable material in order to preserve the achieved lens focal length.

Claim 9 (currently amended): The method of Claim 4 wherein the step of applying the first and second coats of micro-lens suitable material comprise the step of spin coating a micro-lens suitable material onto the semiconductive circuit.

Claim 10 (currently amended): The method of Claim 4 4 wherein the step of imparting the a first lens formation pattern onto the first coat of micro-lens suitable material comprises the steps of:

placing a first formation mask comprising the first lens formation pattern proximate to the first coat of micro-lens suitable material;
aligning the first formation mask relative to the semiconductive circuit; and
illuminating the first formation mask with radiation.

Claims 11-32 (canceled).

Claim 33 (new): The method of Claim 4 wherein the first setback from the boundary is less than a setback for a single pass micro-lens formation method.

Claim 34 (new): The method of Claim 4 wherein the second setback from the boundary is less than a setback for a single pass micro-lens formation method.